



100V P-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

V _{(BR)DSS}	R _{DS(on)}	I _D T _A = +25°C
-100V	350mΩ @ V _{GS} = -10V	-1.6A
-1007	450mΩ @ V _{GS} = -6V	-1.4A

Description

This MOSFET is designed to minimize the on-state resistance and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

- Motor Control
- DC-DC Converters
- Power Management Functions
- Uninterrupted Power Supply

Features and Benefits

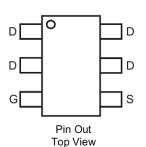
- Fast Switching Speed
- Low Gate Drive
- Low Input Capacitance
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

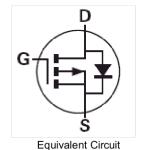
Mechanical Data

- Case: SOT26
- Case Material: Molded Plastic, "Green" Molding Compound;
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals Connections: See Diagram Below
- Terminals: Finish Matte Tin Annealed over Copper Leadframe;
 Solderable per MIL-STD-202, Method 208 ©3
- Weight: 0.018 grams (Approximate)



Top View





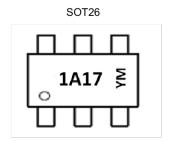
Ordering Information (Note 4)

Part Number	Part Number Compliance		Packaging
ZXMP10A17E6TA	Standard	SOT26	3,000/Tape & Reel

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



1A17 = Product Type Marking Code YM = Date Code Marking Y or \overline{Y} = Year (ex: C = 2015) M or \overline{M} = Month (ex: 9 = September)

Date Code Key

	Year	2015	2016	2017	2018	2019	2020	2021	2022	2023	2024	2025	2026
ĺ	Code	С	D	E	F	G	Н	I	J	K	L	М	N

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Ch	naracteristic		Symbol	Value	Unit
Drain-Source Voltage			V _{DSS}	-100	V
Gate-Source Voltage			V_{GS}	±20	V
		(Note 6)		-1.6	
Continuous Drain Current	V _{GS} = 10V	$T_A = +70^{\circ}C \text{ (Note 6)}$	I _D	-1.3	A
		(Note 5)		-1.3	
Pulsed Drain Current	V _{GS} = 10V	(Note 7)	I _{DM}	-7.7	А
Continuous Source Current (Body Diode) (Note 6)			I _S	-2.1	A
Pulsed Source Current (Body	Diode)	(Note 7)	I _{SM}	-7.7	А

Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Power Dissipation	(Note 5)	D	1.1 8.8	
Linear Derating Factor	(Note 6)	P _D	1.7 13.7	mW/°C
Thermal Resistance, Junction to Ambient	(Note 5)	D	113	°CW
Thermal Resistance, Junction to Ambient	(Note 6)	$R_{ hetaJA}$	73	C/VV
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C	

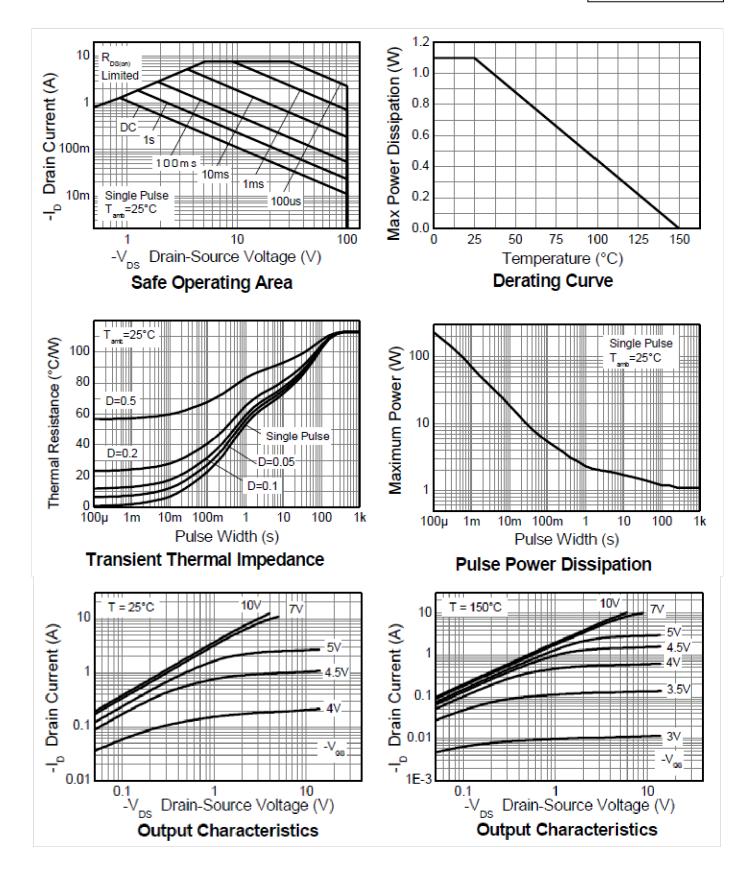
Electrical Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test 0	Condition	
OFF CHARACTERISTICS						•		
Drain-Source Breakdown Voltage	BV _{DSS}	-100	_	_	V	I _D = -250μA, V _{GS} = 0V		
Zero Gate Voltage Drain Current	I _{DSS}	_	_	-0.5	μA	V _{DS} = -100V, V ₀	_{3S} = 0V	
Gate-Source Leakage	I _{GSS}	_	_	±100	nA	$V_{GS} = \pm 20V, V_{D}$	S = 0V	
ON CHARACTERISTICS						•		
Gate Threshold Voltage	V _{GS(th)}	-2	_	-4	V	$I_D = -250 \mu A, V_D$	_S = V _{GS}	
Static Prair Source On Begintones (Nate 9)				0.35		V _{GS} = -10V, I _D =	-1.4A	
Static Drain-Source On-Resistance (Note 8)	R _{DS(ON)}	_	_	0.45	Ω	$V_{GS} = -6V$, $I_D = -1.2A$		
Forward Transconductance (Notes 8 & 9)	9 _{fs}	_	2.8	_	S	V _{DS} = -15V, I _D =	-1.4A	
Diode Forward Voltage (Note 8)	V _{SD}		-0.85	-0.95	V	I _S = -1.7A, V _{GS} = 0V		
Reverse Recovery Time (Note 9)	t _{rr}		33	_	ns	I _S = -1.5A, di/dt = 100A/µs		
Reverse Recovery Charge (Note 9)	Q _{rr}	_	48	_	nC	$I_S = -1.5A$, al/at	= 100A/µs	
DYNAMIC CHARACTERISTICS (Note 9)						•		
Input Capacitance	C _{iss}	_	424	_	pF	501/11	-01/	
Output Capacitance	Coss	_	36.6	_	pF	$V_{DS} = -50V, V_{GS} = 0V$ - F = 1MHz		
Reverse Transfer Capacitance	C _{rss}	_	29.8	_	pF	T - HVIHZ		
Total Gate Charge (Note 10)	Qg	_	7.1	_	nC	V _{GS} = -6V		
Total Gate Charge (Note 10)	Qg	_	10.7	_	nC		V _{DS} = -50V	
Gate-Source Charge (Note 10)	Qgs		1.7	_	nC	$V_{GS} = -10V$ $I_{D} = -1.4A$		
Gate-Drain Charge (Note 10)	Q _{gd}	_	3.8	_	nC			
Turn-On Delay Time (Note 10)	t _{D(on)}		3	_	ns	<u>'</u>		
Turn-On Rise Time (Note 10)	t _r	_	3.5	_	ns	V _{DD} = -50V, V _{GS} = -10V		
Turn-Off Delay Time (Note 10)	t _{D(off)}	_	13.4	_	ns	$I_D = -1A$, $R_G \cong 6$	Ω	
Turn-Off Fall Time (Note 10)	t _f		7.2	_	ns	1		

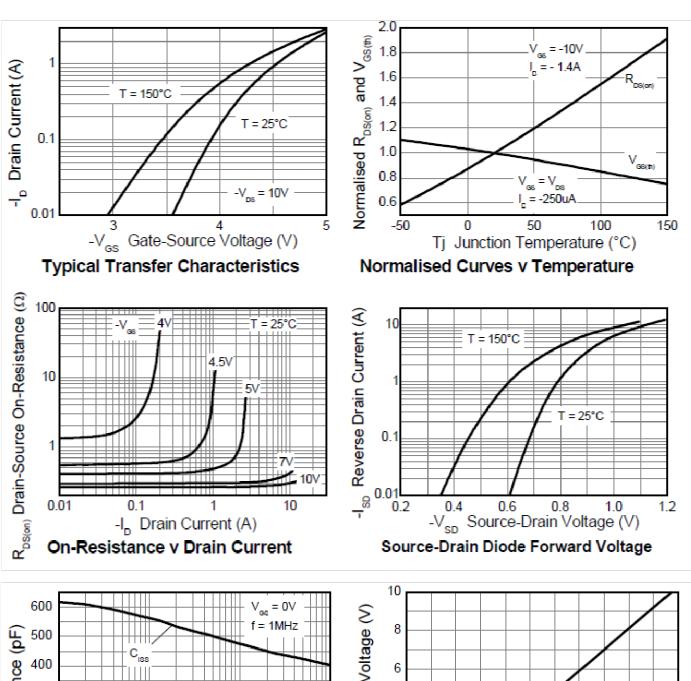
Notes:

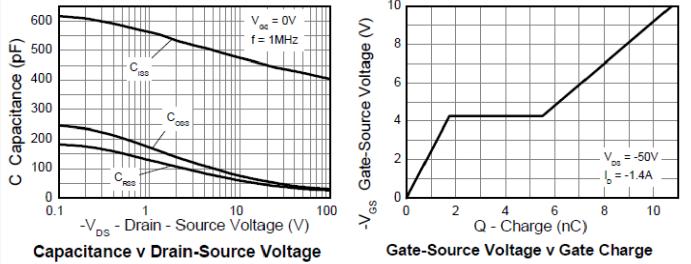
- 5. For a device surface mounted on 25mm x 25mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions; the device is measured when operating in a steady-state condition.
- 6. Same as Note 5, except the device is measured at $t \le 5$ sec.
- 7. Same as Note 5, except the device is pulsed with D = 0.05 and pulse width 10µs. The pulse current is limited by the maximum junction temperature.
- 8. Measured under pulsed conditions. Pulse width $\leq 300 \mu s$; duty cycle $\leq 2\%$.
- 9. For design aid only, not subject to production testing.
- 10. Switching characteristics are independent of operating junction temperatures.





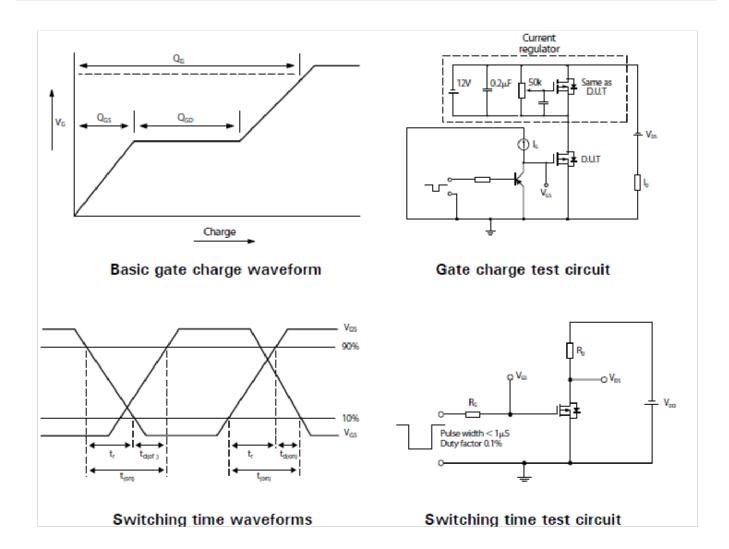








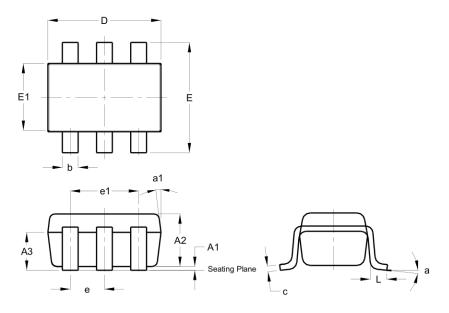
Test Circuits





Package Outline Dimensions

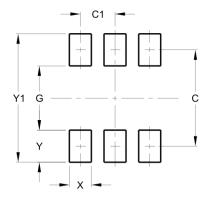
 $Please\ see\ AP02002\ at\ http://www.diodes.com/datasheets/ap02002.pdf\ for\ the\ latest\ version.$



	SOT26							
Dim	Min	Max	Тур					
A1	0.013	0.10	0.05					
A2	1.00	1.30	1.10					
A3	0.70	0.80	0.75					
b	0.35	0.50	0.38					
С	0.10	0.20	0.15					
D	2.90	3.10	3.00					
е	-	-	0.95					
e1	-	-	1.90					
E	2.70	3.00	2.80					
E1	1.50	1.70	1.60					
L	0.35	0.55	0.40					
а	-	-	8°					
a1	-	-	7°					
All	Dimen	sions	in mm					

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
С	2.40
C1	0.95
G	1.60
X	0.55
Υ	0.80
Y1	3 20



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